

# MTM23110

## Silicon P-channel MOSFET

For switching circuits

### ■ Features

- Low voltage drive (1.8 V, 2.5 V, 4 V)
- Realization of low on-resistance, using extremely fine process

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	$V_{DSS}$	-12	V
Gate-source surrender voltage	$V_{GSS}$	$\pm 8$	V
Drain current	$I_D$	-4.0	A
Peak drain current *1	$I_{DP}$	-16	A
Power dissipation *2	$P_D$	500	mW
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \*1: Pulse width  $\leq 10 \mu\text{s}$ , Duty Cycle  $\leq 1\%$

\*2: Measuring on ceramic substrate at  $40 \text{ mm} \times 38 \text{ mm} \times 0.1 \text{ mm}$

Absolute maximum rating without heat sink for  $P_D$  is 150 mW

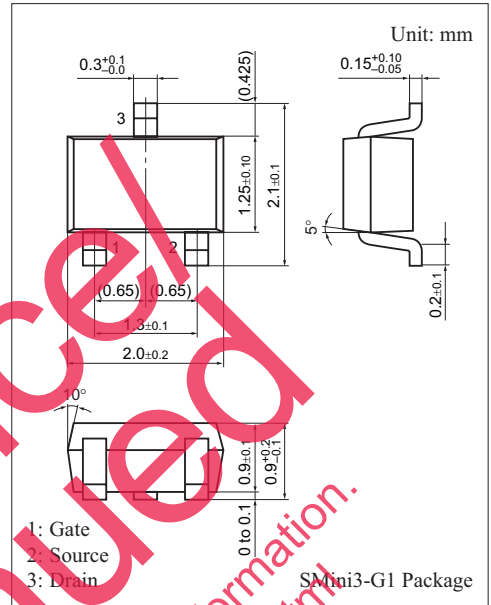
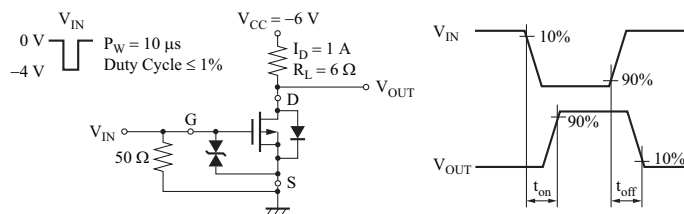
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	$V_{DSS}$	$I_D = -1 \text{ mA}, V_{GS} = 0$	-12			V
Drain-source cutoff current	$I_{DSS}$	$V_{DS} = -12 \text{ V}, V_{GS} = 0$			-1.0	$\mu\text{A}$
Gate-source cutoff current	$I_{GSS}$	$V_{GS} = \pm 6.4 \text{ V}, V_{DS} = 0$			$\pm 10$	$\mu\text{A}$
Gate threshold voltage	$V_{TH}$	$I_D = -1.0 \text{ mA}, V_{DS} = -6.0 \text{ V}$	-0.3	-0.65	-1.0	V
Drain-source ON resistance *1	$R_{D(Son)}$	$I_D = -1 \text{ A}, V_{GS} = -4.0 \text{ V}$		30	40	m $\Omega$
		$I_D = -0.5 \text{ A}, V_{GS} = -2.5 \text{ V}$		35	55	
		$I_D = -0.2 \text{ A}, V_{GS} = -1.8 \text{ V}$		50	75	
Forward transfer admittance *1	$ Y_{fs} $	$I_D = -1.0 \text{ A}, V_{DS} = -10 \text{ V}, f = 1 \text{ kHz}$	3.5			S
Short-circuit forward transfer capacitance (Common source)	$C_{fs}$			1200		pF
Short-circuit output capacitance (Common source)	$C_{oss}$	$V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		110		pF
Reverse transfer capacitance (Common source)	$C_{rss}$			110		pF
Turn-on time *2	$t_{on}$	$V_{DD} = -6 \text{ V}, V_{GS} = 0 \text{ V to } -4 \text{ V}, I_D = -1 \text{ A}$		50		ns
Turn-off time *2	$t_{off}$	$V_{DD} = -6 \text{ V}, V_{GS} = -4 \text{ V to } 0 \text{ V}, I_D = -1 \text{ A}$		300		ns

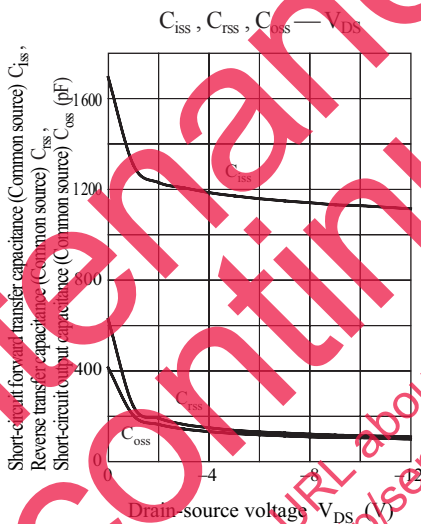
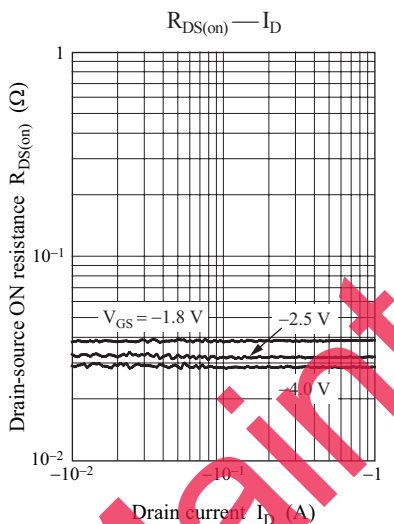
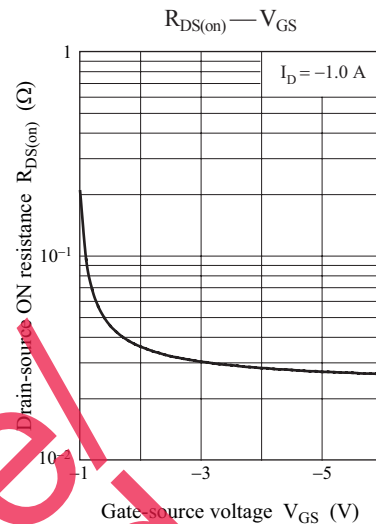
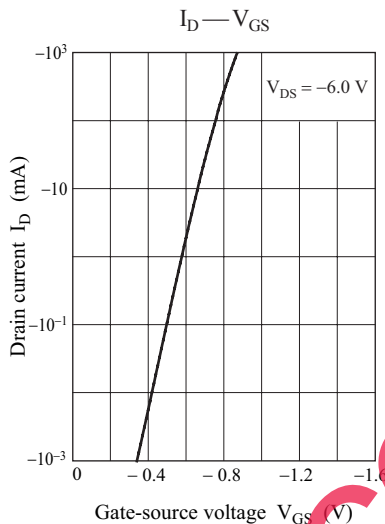
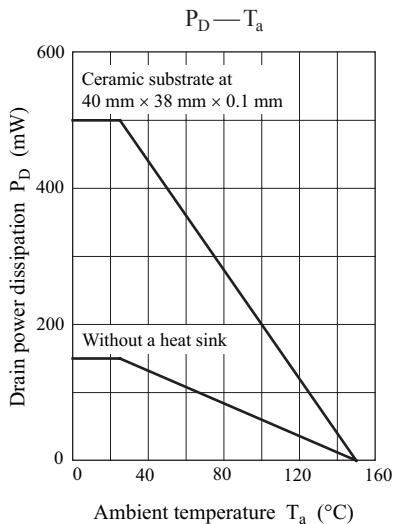
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Pulse measurement: Pulse width  $< 300 \mu\text{s}$ , Duty Cycle  $< 2\%$

\*2:  $t_{on}, t_{off}$  measurement circuit



Marking Symbol: DM



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